

ICS 31.080.10  
CCS L 43



**NATIONAL STANDARD OF THE  
PEOPLE'S REPUBLIC OF CHINA**

**GB/T 6351-1998**

Replacing GB/T 6351-1986

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**Semiconductor devices. Discrete devices. Part 2: Rectifier diodes  
Section One. Blank detail specification for rectifier diodes(including  
avalanche recti-fier diodes)1, ambient and case-rated, up to 100A**

**(English Translation)**

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### What this standard covers

This standard specifies a detailed specification of the basic principles of the development environment or shell rated rectifier diodes (including avalanche rectifier diodes), to develop all the detailed specifications within the range should be as detailed as possible consistent with the norms of the blank. This standard is GB/T 4589. 1-1989 "discrete semiconductor devices and integrated circuits norms" (IEC 747-10: 1984) and GB/T 12560-1990 "discrete semiconductor devices specification" (IEC 747-11: 1985), a series of blank detail specification relating to one.

### Document data

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